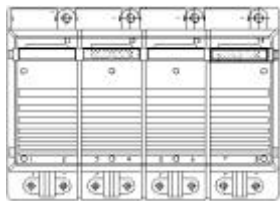


SKiiP 432GH120-2*207CTV ...



SKiiP[®] 2

4-pack - integrated intelligent Power System

Power section

SKiiP 432GH120-2*207CTV

Features

- SKiiP technology inside
- Low loss IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP[®] 2 System)
- IEC 68T.1 (climate) 40/125/56 (SKiiP[®] 2 power section)

- 1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)
- 8) AC connection busbars must be connected by the user; copper busbars available on request

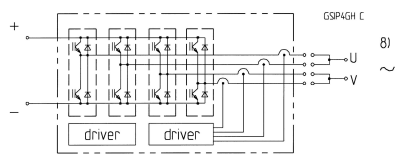
Absolute Maximum Ratings		$T_s = 25\text{ °C}$ unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	Operating DC link voltage	1200	V
$V_{CC}^{1)}$		900	V
V_{GES}		± 20	V
I_C	$T_s = 25\text{ (70) °C}$	400 (300)	A
Inverse diode			
$I_F = -I_C$	$T_s = 25\text{ (70) °C}$	400 (300)	A
I_{FSM}	$T_j = 150\text{ °C}$, $t_p = 10\text{ ms}$; sin.	2880	A
I^2t (Diode)	Diode, $T_j = 150\text{ °C}$, 10 ms	41	kA ² s
$T_j, (T_{stg})$		- 40 (- 25) ... + 150 (125)	°C
V_{isol}	AC, 1 min. (mainterminals to heat sink)	3000	V

Characteristics		$T_s = 25\text{ °C}$ unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V_{CESat}	$I_C = 350\text{ A}$, $T_j = 25\text{ (125) °C}$		2,6 (3,1)	3,1	V
V_{CEO}	$T_j = 25\text{ (125) °C}$		1,2 (1,3)	1,5 (1,6)	V
r_{CE}	$T_j = 25\text{ (125) °C}$		3,8 (5)	4,5 (5,8)	mΩ
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$, $T_j = 25\text{ (125) °C}$		(20)	0,8	mA
$E_{on} + E_{off}$	$I_C = 350\text{ A}$, $V_{CC} = 600\text{ V}$ $T_j = 125\text{ °C}$, $V_{CC} = 900\text{ V}$			105 185	mJ mJ
$R_{CC'} + EE'$	terminal chip, $T_j = 125\text{ °C}$		0,25		mΩ
L_{CE}	top, bottom		7,5		nH
C_{CHC}	per phase, AC-side		2,8		nF

Inverse diode					
$V_F = V_{EC}$	$I_F = 300\text{ A}$, $T_j = 25\text{ (125) °C}$	2,1 (1,9)	2,6		V
V_{TO}	$T_j = 25\text{ (125) °C}$	1,3 (1)	1,4 (1,1)		V
r_T	$T_j = 25\text{ (125) °C}$	2,5 (3)	3,4 (3,9)		mΩ
E_{rr}	$I_C = 350\text{ A}$, $V_{CC} = 600\text{ V}$ $T_j = 125\text{ °C}$, $V_{CC} = 900\text{ V}$		12		mJ
			15		mJ

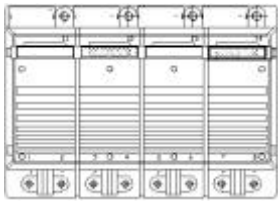
Mechanical data					
M_{dc}	DC terminals, SI Units	6		8	Nm
M_{ac}	AC terminals, SI Units	13		15	Nm
w	SKiiP [®] 2 System w/o heat sink		3,5		kg
w	heat sink		8,5		kg

Thermal characteristics (P16 heat sink; 275m ³ /h); "r" reference to temperature sensor					
$R_{th(j-s)I}$	per IGBT			0,064	K/W
$R_{th(j-s)D}$	per diode			0,188	K/W
$R_{th(s-a)}$	per module			0,033	K/W
Z_{th}	R_i (mK/W) (max. values)	tau _i (s)			
		1	2	3	4
$Z_{th(j-r)I}$		7	50	8	1
$Z_{th(j-r)D}$		21	144	23	1
$Z_{th(r-a)}$		1,6	22	7	2,4
					494
					165
					20
					0,03



Case S 5

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SKiiP® 2

4-pack - integrated intelligent Power System

4-pack integrated gate driver

SKiiP 432GH120-2*207CTV

Gate driver features

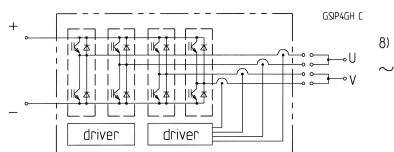
- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- U-option is integrated on left driver, (DC terminals at bottom; refer to case drawing)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 68T.1 (climate) 25/85/56 (SKiiP® 2 gate driver)

Absolute Maximum Ratings			
Symbol	Conditions	Values	Units
V_{S1}	stabilized 15 V power supply	18	V
V_{S2}	unstabilized 24 V power supply	30	V
V_{iH}	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/ μ s
V_{isolIO}	input / output (AC, r.m.s., 2s)	3000	Vac
V_{isol12}	output 1 / output 2 (AC, r.m.s., 2s)	1500	Vac
f_{max}	switching frequency	20	kHz
$T_{op} (T_{stg})$	operating / storage temperature	- 25 ... + 85	°C

Characteristics				(T _a = 25 °C)		
Symbol	Conditions	min.	typ.	max.	Units	
V_{S1}	supply voltage stabilized	14,4	15	15,6	V	
V_{S2}	supply voltage non stabilized	20	24	30	V	
I_{S1}	$V_{S1} = 15 V$	$210+320*f/f_{max}+1,3*(I_{AC}/A)$			mA	
I_{S2}	$V_{S2} = 24 V$	$160+220*f/f_{max}+1,0*(I_{AC}/A)$			mA	
V_{iT+}	input threshold voltage (High)	11,2			V	
V_{iT-}	input threshold voltage (Low)	5,4			V	
R_{IN}	input resistance	10			k Ω	
$t_{d(on)IO}$	input-output turn-on propagation time	1,2			μ s	
$t_{d(off)IO}$	input-output turn-off propagation time	1,6			μ s	
$t_{pERRRESET}$	error memory reset time	9			μ s	
t_{TD}	top / bottom switch : interlock time	3,3			μ s	
$I_{analogOUT}$	8 V corresponds to max. current of 15 V supply voltage (available when supplied with 24 V)	400			A	
$I_{Vs1outmax}$	output current at pin 12/14	50			mA	
I_{A0max}	logic low output voltage	5			mA	
V_{0l}	logic high output voltage	0,6			V	
V_{0H}	logic high output voltage	30			V	
I_{TRIPSC}	over current trip level ($I_{analog OUT} = 10 V$)	500			A	
I_{TRIPLG}	ground fault protection				A	
T_{tp}	over temperature protection	110	120		°C	
U_{DCTRIP}	trip level of U _{DC} -protection ($U_{analog OUT} = 9 V$); (option)	900			V	

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